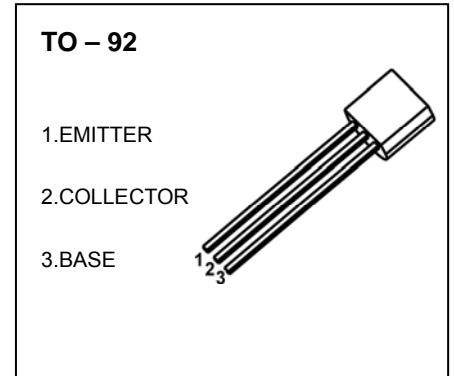




BC369 TRANSISTOR (PNP)

FEATURES

- High Current
- Low Voltage



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1	A
P _C	Collector Power Dissipation	0.625	W
R _{θJA}	Thermal Resistance From Junction To Ambient	200	°C/W
T _j	Junction temperature	150	°C
T _{stg}	storage temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-25V, I _E =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-10	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-0.5A	85		375	
	h _{FE(2)}	V _{CE} =-10V, I _C =-5mA	50			
	h _{FE(3)}	V _{CE} =-1V, I _C =-1A	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-0.1A			-0.5	V
Base-emitter voltage	V _{BE}	I _C =-1A, V _{CE} =-1V			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=35MHz	65			MHz